

IN THE CLAIMS:

Claims 4 and 17 have been cancelled. Claims 1-3, 4-16, and 18-21 have been amended herein. All of the pending claims 1 through 21 are presented below. This listing of claims will replace all prior versions and listings in the application. Please enter these claims as amended.

1. (Currently Amended) A method for fabricating a mask comprising:
forming a substrate including:
a first layer of attenuating material over saidthe substrate;
a second layer of attenuating material over saidthe first layer of attenuating material; and
an opaque layer over saidthe second layer of attenuating material;
etching saidthe substrate to form at least one completely transmissive region;
etching saidthe substrate to form at least one slightly attenuated region, saidthe etching including
forming a ~~see~~^ond-patterned resist over saidthe substrate; and
etching saidthe substrate to form at least one highly attenuated region.
2. (Currently Amended) The method according to claim 1, wherein etching saidthe substrate to form saidthe at least one completely transmissive region comprises forming a first patterned resist over saidthe opaque layer of saidthe substrate and etching saidthe substrate to form a plurality of isolated completely transmissive regions and a plurality of ~~elosely~~closely spaced completely transmissive regions.
3. (Currently Amended) The method according to claim 2, wherein etching saidthe substrate to form saidthe at least one slightly attenuated region comprises removing portions of saidthe opaque layer and saidthe second layer of attenuating material to form a plurality of slightly attenuated regions, each of saidthe plurality of slightly attenuated regions being positioned at an edge defining one of saidthe plurality of isolated completely transmissive regions.

4. (Deleted without prejudice)

5. (Currently Amended) The method according to claim 2, wherein etching saidthe substrate to form saidthe at least one highly attenuated region comprises removing portions of saidthe opaque layer to form a plurality of highly attenuated regions, each of saidthe plurality of highly attenuated regions being positioned at an edge defining one of saidthe plurality of closely-closely spaced completely transmissive regions.

6. (Currently Amended) The method according to claim 5, wherein etching saidthe substrate to form saidthe plurality of highly attenuated regions comprises forming a third patterned resist over saidthe substrate.

7. (Currently Amended) The method according to claim 1, wherein providforming saidthe substrate further comprises providforming saidthe substrate comprising to include an etch stop layer between saidthe first layer of attenuating material and saidthe second layer of attenuating material.

8. (Currently Amended) The method according to claim 7, wherein etching saidthe substrate to form saidthe at least one completely transmissive region comprises forming a first patterned resist over saidthe opaque layer of saidthe substrate and etching saidthe substrate to form a plurality of isolated completely transmissive regions and a plurality of closely-closely spaced completely transmissive regions.

9. (Currently Amended) The method according to claim 8, wherein etching saidthe substrate to form saidthe at least one slightly attenuated region comprises removing portions of saidthe opaque layer and saidthe second layer of attenuating material in a single etch step to form a plurality of slightly attenuated regions, each of saidthe plurality of slightly attenuated regions being positioned at an edge defining one of saidthe plurality of isolated completely transmissive regions.

10. (Currently Amended) The method according to claim 9, wherein etching said the substrate to form said the at least one highly attenuated region comprises removing portions of said the opaque layer to form a plurality of highly attenuated regions, each of said the plurality of highly attenuated regions being positioned at an edge defining one of said the plurality of closely closely spaced completely transmissive regions.

11. (Currently Amended) The method according to claim 10, wherein etching said the substrate to form said the plurality of highly attenuated regions comprises forming a third patterned resist over said the substrate.

12. (Currently Amended) A attenuated phase shift mask comprising:
a transparent substrate;
a plurality of isolated completely transmissive regions and a plurality of other regions;
a plurality of slightly attenuated regions, each of said the plurality of slightly attenuated regions being formed at an edge defining one of said the plurality of isolated completely transmissive regions;
a plurality of completely transmissive regions; and
a plurality of highly attenuated regions, each of said the plurality of highly attenuated regions being formed at an edge defining one of said the plurality of isolated completely transmissive regions, said the plurality of highly attenuated regions comprising a first layer of attenuating material, a layer of etch stop material, and a second layer of attenuating material.

13. (Currently Amended) The attenuated-phase shift mask of claim 12, further comprising a plurality of opaque regions.

14. (Currently Amended) The ~~attenuated~~-phase shift mask of claim 13, wherein ~~said~~the plurality of opaque regions comprise chromium.

15. (Currently Amended) The ~~attenuated~~-phase shift mask of claim 12, wherein ~~said~~the transparent substrate comprises a material selected from a group consisting of quartz, fused silica, and glass.

16. (Currently Amended) The ~~attenuated~~-phase shift mask of claim 12, wherein ~~said~~the plurality of slightly attenuated regions comprises a layer of attenuating material selected from a group consisting of chromium oxynitride and chromium fluoride.

17. (Deleted without prejudice)

18. (Currently Amended) The ~~attenuated~~-phase shift mask of claim ~~17~~ 12, wherein ~~said~~the first layer of attenuating material is selected from a group consisting of chromium oxynitride and chromium fluoride and ~~said~~the second layer of attenuating material comprises molybdenum silicide oxynitride.

19. (Currently Amended) The ~~attenuated~~ phase shift mask of claim 12, wherein ~~said~~the plurality of slightly attenuated regions comprises a layer of attenuating material and a layer of etch stop material.

20. (Currently Amended) The ~~attenuated~~ phase shift mask of claim 19, wherein ~~said~~the layer of attenuating material is selected from a group consisting of chromium oxynitride and chromium fluoride and ~~said~~the layer of etch stop material comprises silicon dioxide.

21. (Currently Amended) The ~~attenuated~~ phase shift mask of claim 12, wherein ~~said~~the first layer of attenuating material is selected from a group consisting of chromium oxynitride and chromium fluoride, ~~said~~the layer of etch stop material comprises silicon dioxide, and ~~said~~the second layer of attenuating material comprises molybdenum silicide oxynitride.